CeM nN i₄: an impostor half-m etal

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Recent experiments show CeM nN i_4 to have a nearly integer magnetic moment and a relatively large transport spin polarization, as probed by Andreev rejection, suggesting that the material is a half metal or close to it. However, the calculations reported here show that it is not a half metal at all, but rather a sem in etal of an unusual nature. Phonon properties should also be quite unusual, with rattling low-frequency M n modes. Nontrivial transport properties, including a large therm olectric gure of merit, ZT; are predicted in the ferrom agnetic state of the well ordered stoichiom etric CeM nN i_4

Recently, Singh et al¹ have measured the magnetic and transport properties of a novel ferrom agnetic m aterial, CeM nN i4: The most striking observations are that the m easured m agnetic m om ent is 4.94_{B} =form ula, rem arkably close to an integer m agnetization of 5 $_{\rm B}$; and at the same time Andreev re ection is suppressed in a way typical of highly polarized ferrom agnets. The degree of spin polarization, deduced in the standard m anner, was up to 65%, a relatively large number. These observations together suggest that CeM nN i might be a halfmetal. On the other hand, another, less obvious, observation cast doubt on such a simple interpretation: the resistivity as measured in Ref. 1 rapidly grows from zero tem perature to $T_{\rm C}$ = 148 K, at a rate up to 2 cm/K, characteristic of bad metals, with a very large residual resistivity of 0.24 m am. At the same time, above T_C the temperature coe cient of the resistivity drops practically discontinuously to a value smaller than 0.06 cm /K, a 1.5 order of m agnitude change! Indeed, such large changes in the tem perature coe cient resistivity at T c have been previosly encountered only near a m etal-insulator transition (cf: collosal m agnetoresistance, CMR). Som e halfm etals m ay exhibit large changes of the resistivity slope near T_C without a m etal-insulator transition, but the change is in the opposite direction².

B and structure calculations for this material can be expected to shed som e light on the puzzling features described above. They do indeed, and in a rather unexpected way. In this paper I report such calculations and discuss their ram i cations.

C eM nN i_4 crystallizes in the F $\overline{43m}$ group (# 216). Its structure can be derived from the Heusler structure ABCD; where C e and M n occupy A and B positions, and N isits between C and D (plus three sym m etry equivalent positions), F ig.1. A sone can see, N i form s corner-sharing tetrahedra, sim ilar to the spinel structure. The structure has one free param eter, the N iposition. If this position is exactly equal to (5/8, 5/8, 5/8) the lengths of the N i-C e and N i-M n bonds are exactly the sam e. A s w e will see, the optim ized structure is very close to this, despite the fact that C e has about 30% larger atom ic radius than M n. T his is yet another hard to understand property of this com pound. I have perform ed full-potential LAPW calculations, using the W IEN package³ and Perdew-Burke-

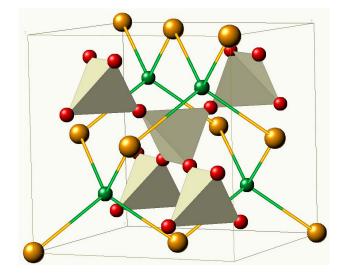


FIG.1: Crystal structure of C eM nN i_4 . Large brown spheres denote the C e atom s, the sm all green ones M n, and the tetrahedra are form ed by the N i atom s, denoted by the sm all red spheres. (color online)

E mzerhof⁴ gradient-corrected exchange-correlation potential. Mu n-tin radiiof2.5 a _B for C e and M n and 2.23 a_B for N iwere used, the basis set included planew aves up to RK_{max} = 7 with APW local orbitals, and integration in k space was performed using the tetrahedron m ethod with 286 inequivalent points (21x21x21 m esh)⁵.

The nonm agnetic density of states (DOS) of C eM nN i4 is shown in Fig.2. One can clearly see that C e fbands are about 1 eV above the Ferm i level, indicating their delocalized character with no need of applying Hubbard-type correction (e.g., within LDA+U). It is further seen that M n form s a relatively narrow band (0.25-0.30 eV), while the Nibands are at least 4 eV wide (I will explain the origin of the Mn band narrowing later). Moreover, the M n bands are pinned to the Ferm i level, and are largely responsible for the very high DOS at the Ferm i level (10 states/eV spin form ula, or 2 states/eV spin per 3d m etal ion). Recalling that 3d transition metals have Stoner factors of the order of 1 eV, it is obvious that even after diluting with the less magnetic Ce the material should be very strongly m agnetic. I thus proceed with m agnetic calculations and nd the band structure shown in Fig.

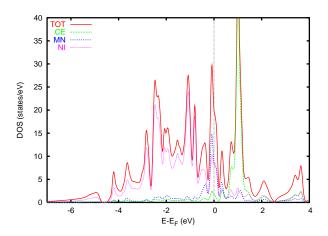


FIG. 2: Density of states of nonmagnetic CeM nN i_4 . (color online)

3 and 4. First, the ferrom agnetic structure is found to be stabilized by a huge energy gain of 1.87 eV per formula. Second, the total calculated m agnetization is 4.92 $_{\rm B}$ / form ula, in nearly perfect agreem ent with the experiment, and indeed very close to an integer value. The mom ent is distributed like this: M n carries approxim ately 4 $_{\rm B}$, four N itogether about 1.2 $_{\rm B}$ and C e is polarized antiferrom agnetically with a moment of 0.2 _B : C learly the magnetic engine in this compound is Mn, whose d states are fully split by about 3 (!) eV^6 . Ce plays the role of a cation in this compound, donating its one f-electron to Mn. This can be veried by taking the charges inside each MT sphere and distributing the interstitial charge proportionally to the MT sphere volumes, which yields 12e;Q_{M n} 0:6e;Q_{N i} 0:15e:As a result, QCe M n has 6 d-electrons, and full exchange splitting on M n site results in 5 spin-up and one spin-down electron. Ce f (and d)-states are above the Ferm i level, so they hybridize more with the higher-lying 3d metal spin-down states (mostly N i) than with the spin-up states, and the form er acquire m ore of C e character. This explains the antiferrom agnetic polarization on Ce.

At this point it is worth mentioning that all calculations described above and below were performed in the structure obtained after optim izing the positions of N iby m in in izing the total energy in the ferrom agnetic state. It appears that the optim alposition of N i in lattice coordinates is (0.624, 0.624, 0.624), and symmetry equivalent positions. This is spectacularly close to the \ideal" position of (5/8, 5/8, 5/8). M oreover, the corresponding A_{1g} phonon of Nidoes not appear to be particularly soft - the calculated frequency is about 165 cm 1 ; a very regular num ber for an interm etallic com pound with 3d metals. If one substitutes M n by Ce, the resulting structure, provided that Nioccupies the ideal position above, is the well known Laves phase. In fact, such a phase $(C \in N_2)$ does form ⁷, with the lattice parameter practically identical (within 3%) to that of CeM nNi4: This proves that the lattice param eter of the latter is de ned

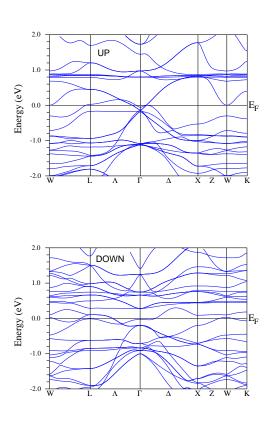


FIG. 3: Band structure of the ferrom agnetic CeM nN i_4 in the optim ized structure. Top panel: spin up. Bottom panel: spin down.

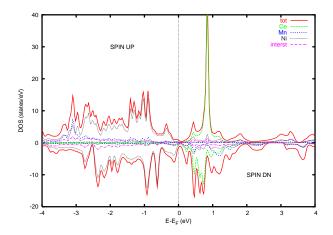


FIG.4: Density of states of the ferrom agnetic CeM nN $i_4\,$ in the optim ized structure. (color online)

by the Ce-N i interaction. A fier one Ce is substituted by a M n with its 30% smaller metal radius, M n appears in a cage much larger than is needed for norm al metallic bonding. Indeed, know n M n-N i binaries (M nN i, M nN i₃) are characterized by the N i-M n bonds of the order of 4.8 a_B ; com pared to nearly 5.5 a_B in CeM nN i₄: Thus, M n in CeM nN i₄ is a \rattling" ion, sim ilar, for example, to

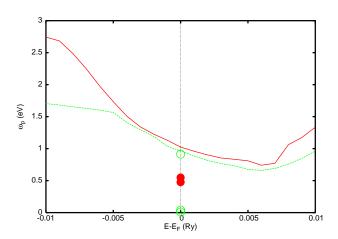


FIG. 5: The plasm a frequencies of ferror agnetic C eM nN i₄ in the optimized structure. G meen dashed (red solid) lines show the spin-up (spin-down) components. Symbols show a band decomposition at the Fermilevel: open: spin-up; lled: spin-down. (color online)

La rattling in therm celectric skuttenudites. This anom alously large distance from M n to its nearest neighbors explains why the M n bands in C eM nN $\rm i_4$ are so narrow .

Even a cursory glance at the density of states (Fig. 4) and especially at the band structure (Fig. 3) of the ferrom agnetic C eM nN i4 reveals that despite the nearlyinteger magnetic moment it could not be farther from a half m etal. W hat is actually happening is that in both spin channels the Ferm i level, rather accidentally, falls inside a deep pseudogap (about 0.3 eV wide), thus making this material more a sem in etal than half metal (except that in a classical sem in etal, like Bi, there is at least a direct gap, although the valence band and the conductivity bands have a small indirect overlap, whereas in CeMnNi4 there is no gap at all). The DOS at the Ferm i level is $N_{*} = 0.85$ states/eV .form ula, $N_{*} = 1.16$ states/eV .form ula, corresponding to an electronic speci c heat coe cient of 4.7 m J/m olK 2 ; or 0.8 m J/g-atom K 2 : This is a very smallDOS, characteristic rather of doped sem iconductors than of m etals.

Note that the corresponding spin polarization of the DOS is 16%; far from the observed 66%¹. Of course, one has to keep in m ind that the Andreev re ection is sensitive only to the transport spin polarization, and likely, given the high resistivity of current samples, to the di usive transport spin polarization⁸. Let m e rem ind the reader that the latter can be expressed in terms of the spin-dependent contribution to the plasm a frequency, $P_{diff} = (!_{p''}^2 - !_{p\#}^2) = (!_{p''}^2 + !_{p\#}^2)$: Should the Ferm ivelocities for the two spin channels be drastically di erent, that could explain the observed high transport spin polarization. However, direct calculations yield the opposite result (Fig.5): $!_{p"} = 1.07 \text{ eV}$, $!_{p\#} = 1.10 \text{ eV}$, corresponding to 3% spin polarization. This means that the Ferm i velocities are very close for both spins and actually relatively small for a typical transition metal:

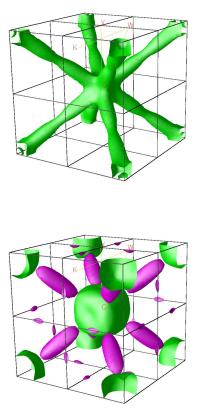


FIG.6: The Ferm isurfaces of CeM nN i4 for spin-up (top) and spin-down (bottom). Only one band is shown for the spin up and two for the spin down. O ther bands create just barely noticeable Ferm isurface pockets. In order to produce a large number of eigenvalues I used LM TO bands for this plot; I have veried that the dierence beween LM TO and LAPW bands is too sm all to be visible on the scale of this gure. (color online)

 $v_{\rm F}$ = 2:1 10^7 cm/sec, $v_{\rm F}$ = 1:9 10^7 cm/sec. The m essage here is that the low DOS occurs not because of light electrons, but because of the sm all Ferm i surfaces. Indeed, only three bands, one for the spin-up and two for the spin-down channel form noticeable Ferm i surface pockets, shown in Fig. 6. This emphasizes again the analogy with sem in etals.

W hile the calculations de nitely do not agree with the measured spin polarization, this does not necessarily mean that either are wrong. The accepted technique for analyzing Andreev re ection data assumes an equal barrier strength for both spin channels. As has been pointed out previously⁹, this assumption is not always justi ed and may change the results substantially.

O ne cannot exclude sam ple problem s either; the tem – perature dependence reported in Ref. 1 hints at that. Indeed, the extrem ely weak tem perature dependence of the resistivity above T_c im plies that there are no low – energy excitations (phonons orm agnons) that could scat-

ter electrons (otherwise one would have a linear T dependence, as in the B loch-G runeisen form ula). On the other hand, if such excitations were present below T_C but disappeared at the phase transition, a negative temperature coe cient would be expected just near the transition tem perature, since the electron-scattering will be not present above $T_{\rm C}$. On the other hand, if the resistivity were mainly due to static defects, the tem perature dependence of the resistivity could be explained by a gradual decrease of the carrier concentration with tem perature in the ferrom agnetic phase, from T = 0 to T_c , which would have then to remain constant above $T_{\rm C}$. However, the e ective carrier concentration, (n=m) eff; is nothing but the plasm a frequency expressed in di erent units, and, as discussed above, the plasm a frequency in CeM nN i4 is much larger in the param agnetic state¹⁰, which would yield a decrease, not increase of with the tem perature, with a resistivity m in imum near $T_{\rm C}$ (as, for instance, in $Fe_xCo_1 \times S_2$; see Ref. 2).

On the other hand, the behavior below $T_{\rm C}$ is reminiscent of the CMR m anganates and some magnetic semiconductors, where large residual resistivity is also combined with a rapidly growing resistivity below $T_{\rm C}$. The low e ective carrier density in CeMnNi₄ supports this analogy. However, in CMR materials $T_{\rm C}$ coincides with a metal-insulator transition, in most cases resulting in a strong (orders of magnitude) maximum of resistivity near $T_{\rm C}$, instead of rather at behavior above $T_{\rm C}$ in CeMnNi₄, or in even more complicated temperature dependences driven by various structural transform ations. Nevertheless, spatial inhom ogenuity and percolation effects, known to be operative in manganates, may play an important role in CeMnNi₄ too. All this emphasizes

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- ³ P.B laha, K.Schwarz, G.K.H.M adsen, D.K vasnicka, and J.Luitz, W ien2k-05, an Augmented Plane W ave + Local Orbitals Program for Calculating Crystal Properties (K arlheinz Schwarz, Techn. Universitat W ien, Austria) ISBN 3-9501031-1-2.
- ⁴ JP.Perdew, K.Burke and M.Emzerhof, Phys.Rev.Lett. 77, 3865 (1996).
- ⁵ Since C e f states are empty and rem oved from the Ferm i level one can conjecture that spin-orbit e ects are not in portant. Indeed, I have perform ed second-variational calculations with spin-orbit and found the e ect to be negligible. By the same token, one does not expect LDA + U (f) calculations to be any di erent from the regular LDA, and not even m ore relevant, given delocalized nature of the f states in this com pound. Out of curiosity, I have perfored LDA + U caculation in the Around-M ean-Field approxim ation, appropriate for a m etal like this, and using

again the unusual character of this material and calls for further experimental studies.

Let m e now sum m arize the results of the calculations. First, despite the apparent resemblance to a half m etal, CeM nN i4 is not one. Its m agnetic m om ent is sim ply accidentally nearly integer. Second, CeM nN i4 exhibits a very deep pseudogap at the Ferm i level, with the DOS dropping to a uniquely low value for an interm etallic com pound. Third, despite the sm allDOS, the Ferm ivelocity is also rather low, which makes C eM nN i4 electronically sim ilar to sem in etals. Intriguingly, the calculated electronic structure and transport properties o er no obvious explanation of the observed tem perature dependence of the resistivity, which, unless one is willing to write this o as a sample problem, represent a very interesting challenge to the theory. Finally, the crystal structure is essentially set by the Ce-Ni cage, with Mn rattling in a cavity much larger than what is appropriate for this ion. These rather unusual characteristics should lead to interesting transport and optical properties. In particular, last but not least, the sim ilarity to sem in etals and presence of rattling phonon modes should make CeM nN i4 a very prom ising low-tem perature therm celectric, provided it can be synthesized in a stoichiom etric and defect-free form . On the other hand, by intentionally introducing defects one can create a material with a very high equilibrium magnetization and very low resistivity, making it a better soft magnetic material than the ferrites. O by jourly, practical applications in this direction would require optim izing the material to raise its Curie tem perature to room tem perature.

The author acknow ledges useful discussions with M . Johannes, D . K hom skii and B . N adgorny.

- U = 1.25 and J = 0.33 eV for C e f (as estimated from the atom ic loop in an LM TO program), and again found practically no change from straight LDA.
- ⁶ A lthough M n d-bands are narrow and very likely correlated, such a large exchange splitting m akes applying LDA + U correction to M n an unnecessary com plication: it would just increase the splitting between the occupied and unoccupied M n states without any interesting e ects at the Ferm i kevel.
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 ¹⁰ In the hypothetical nonm agnetic state the plasm a frequency is drastically larger, than in the ferrom agnetic state. The param agnetic state of C eM nN i₄ is not nonm agnetic, but rather a disordered-local-m om ents states. Still, a rather accidental nature of the pseudogap in the ferrom agnetic calculations strongly suggests that m agnetic disorder should considerably increase !_p.